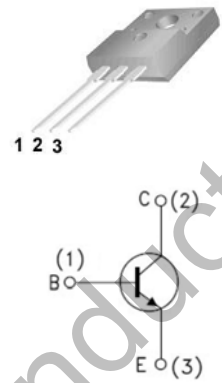


WGF13007


Features:

- High Voltage Capability
- High Switching Speed
- Suitable for Electronic Ballast and Switching Mode Power Supply
- 100% Avalanche Tested

TO-220F



1. Base (B)
2. Collector (C)
3. Emitter (E)



Absolute Maximum Ratings* T_J = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	700	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	9	V
I _C	Collector Current (DC)	8	A
I _{CP}	Collector Current (Pulse)	16	A
I _B	Base Current	4	A
P _C	Collector Dissipation (T _C = 25°C)	80	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-65 ~ 150	°C

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA, I _B = 0	400			V
I _{EBO}	Emitter Cut-off Current	V _{EB} = 9V, I _C = 0			1	mA
h _{FE1} h _{FE2}	DC Current Gain *	V _{CE} = 5V, I _C = 2A V _{CE} = 5V, I _C = 5A	8 5		60 30	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 2A, I _B = 0.4A I _C = 5A, I _B = 1A I _C = 8A, I _B = 2A			1.0 2.0 3.0	V V V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 2A, I _B = 0.4A I _C = 5A, I _B = 1A			1.2 1.6	V V
f _T	Current Gain Bandwidth Product	V _{CE} = 10V, I _C = 0.5A	4			MHz
C _{ob}	Output Capacitance	V _{CB} = 10V, f = 0.1MHz		110		pF
t _{ON}	Turn On Time	V _{CC} = 125V, I _C = 5A			1.6	μs
t _{STG}	Storage Time	I _{B1} = -I _{B2} = 1A R _L = 25Ω			3.0	μs
t _F	Fall Time				0.7	μs

* Pulse Test: PW ≤ 300μs, Duty Cycle ≤ 2%

h_{FE} Classification

Classification	H1	H2
h _{FE1}	15 ~ 28	26 ~ 39

Typical Characteristics

Figure 1. DC Current Gain

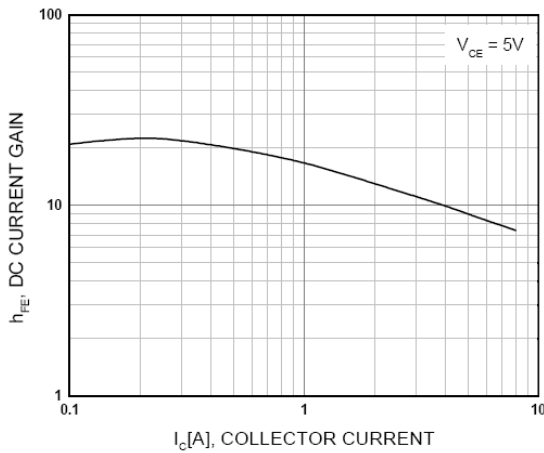


Figure 2. Saturation Voltage

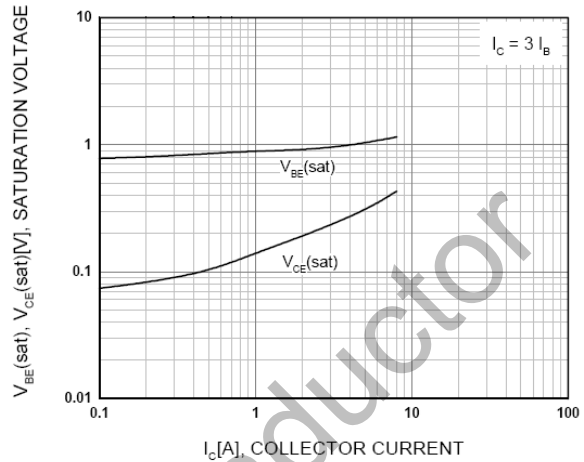


Figure 3. Collector Output Capacitance

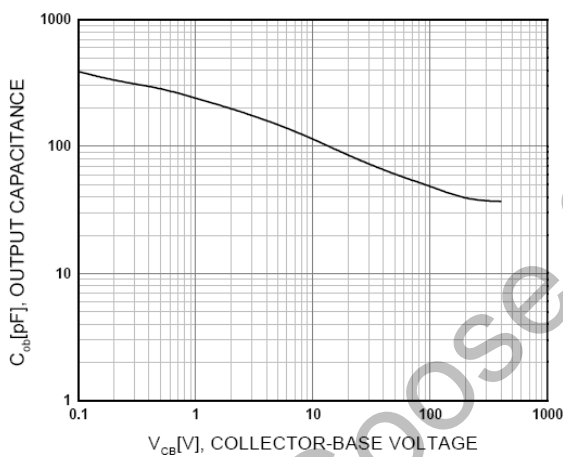


Figure 4. Turn On Time

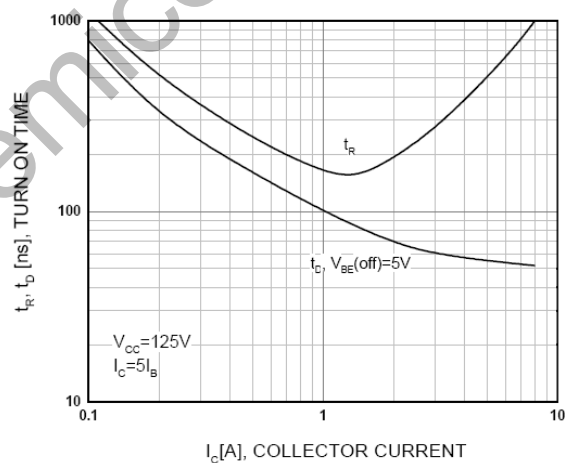


Figure 5. Turn Off Time

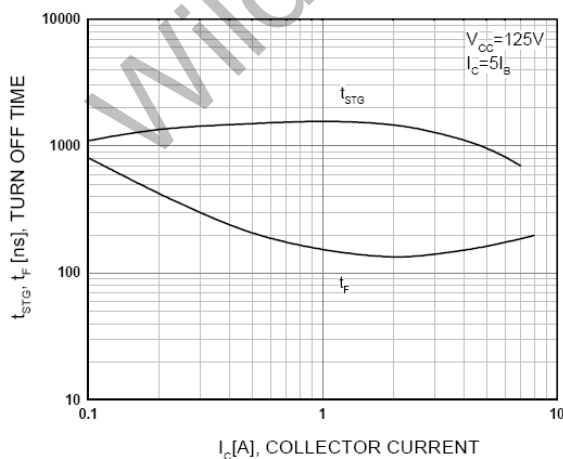
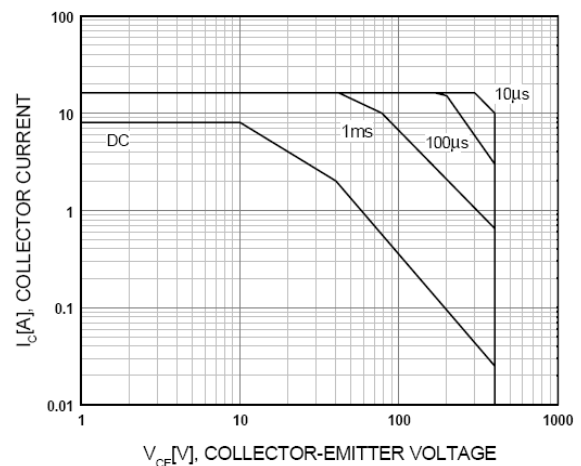


Figure 6. Forward Biased Safe Operating Area



Typical Characteristics

Figure 7. Reverse Biased Safe Operating Area

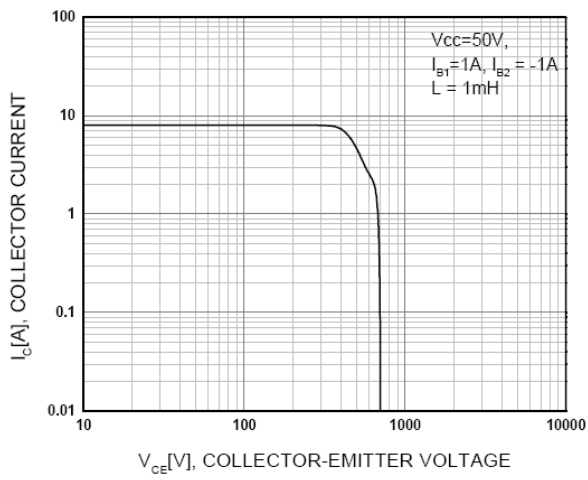
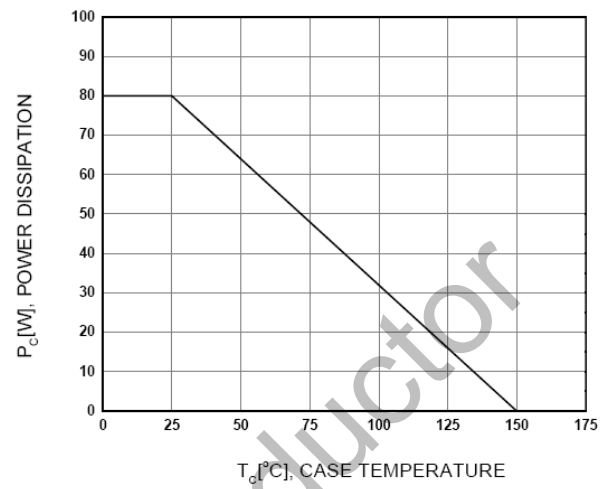


Figure 8. Power Derating

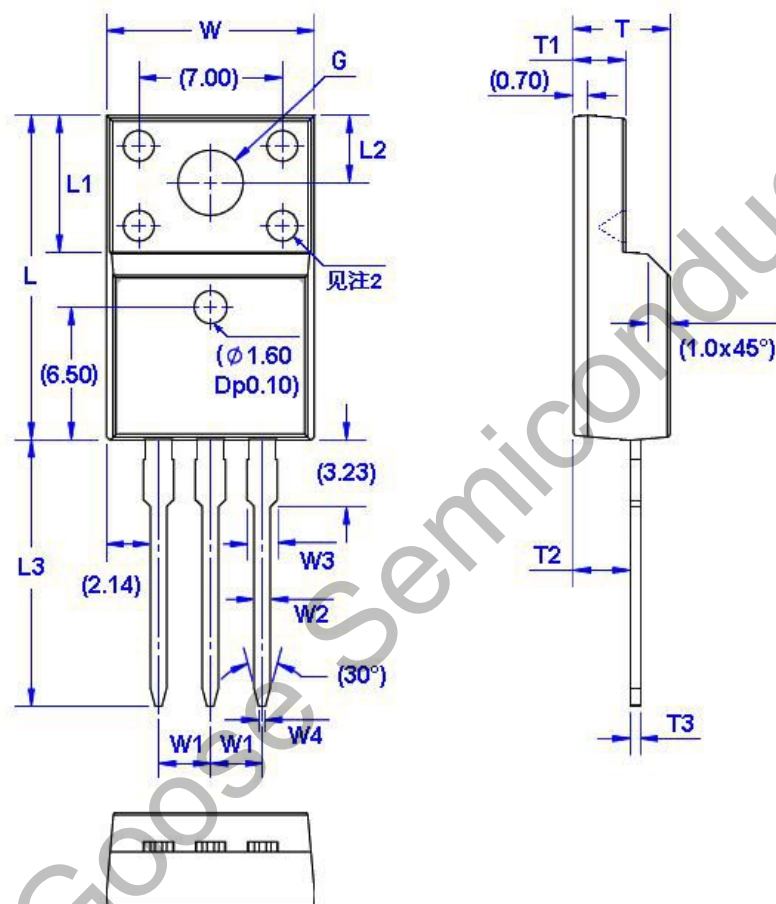


WildGoose Semiconductor

Package Dimension

**TO-220F
(ITO-220AB)**

Unit: mm



Symbol	Size		Symbol	Size		Symbol	Size		Symbol	Size	
	Min	Max		Min	Max		Min	Max		Min	Max
W	9.96	10.36	W4	0.25	0.45	L3	12.78	13.18	T3	0.45	0.60
W1	2.54 (TYP)		L	15.67	16.07	T	4.50	4.90	G(Φ)	3.08	3.28
W2	0.70	0.90	L1	6.48	6.88	T1	2.34	2.74			
W3	1.24	1.47	L2	3.20	3.40	T2	2.56	2.96			